

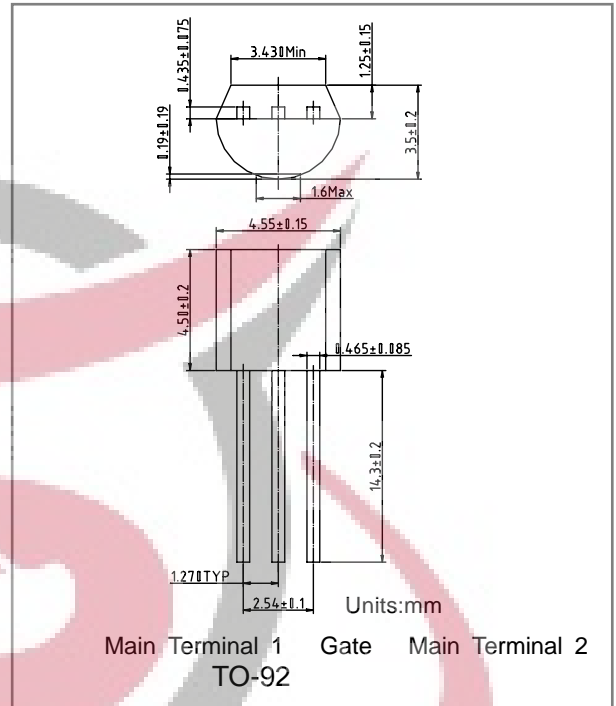
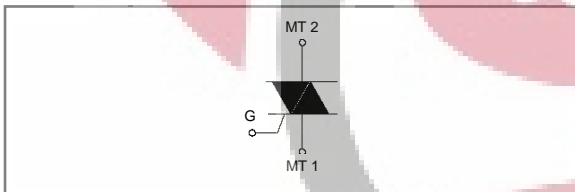
0.8A TRIACS

MAIN FEATURES:

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT(Q1)}$	5	mA

DESCRIPTION

The Z0607 is suitable for low power AC switching applications, such as fan speed, small light controllers... Thanks to low gate triggering current, it can be directly driven by microcontrollers.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)		$T_I=50$ 0.8	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial=25)	F=50Hz t=20ms	9	A
		F=60Hz t=16.7ms	9.5	
I^2t	I^2t Value for fusing	$t_p=10ms$	0.45	A^2s
di/dt	Critical rate of rise of on-state current $I_G=2 \cdot I_{GT}$, $t_r=100ns$	F=120Hz $T_j=110$	20	$A/\mu s$
I_{GM}	Peak gate current	$t_p=20 \mu s$ $T_j=110$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j=110$	0.1	W
T_{sig}	Storage junction temperature range		-40 to +150	
T_j	Operating junction temperature range		-40 to +110	

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

Symbol	Test condition	Quadrant		Value	Unit
I _{GT} (1)	V _D =12V R _L =30	- -	MAX.	5	mA
		IV		7	
V _{GT}		ALL	MAX.	1.3	V
V _{GD}	V _D =V _{DRM} R _L =3.3K T _j =110	ALL	MIN.	0.2	V
I _H (2)	I _T =200mA		MAX.	5	mA
I _L	I _G =1.2I _{GT}	- -	MAX.	10	mA
				20	
dV/dt(2)	V _D =67%V _{DRM} gate open T _j =110		MIN.	10	V/μs
(dV/dt) _c (2)	(dV/dt) _c =0.35A/ms T _j =110		MIN.	1.5	V/μs

STATIC CHARACTERISTICS

Symbol	Test condition			Value	Unit	
V _{TM} (2)	I _{TM} =1.1A	tp=380 μs	T _j =25	MAX.	1.5	V
V _{IG} (2)	Threshold voltage		T _j =110	MAX.	0.95	V
R _d (2)	Dynamic resistance		T _j =110	MAX.	420	m
I _{DRM} I _{RDM}	V _{DRM} =V _{RDM} =600V		T _j =25	MAX.	5	μA
			T _j =110		0.1	

Note 1: minimum IGT is guaranteed at 5% of IGT max.

Note 2: for both polarities of Main Terminal 2 referenced to Main Terminal 1

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-l)}	Junction to lead (AC)	60	/W
R _{th(j-a)}	Junction to ambient	150	/W

PRODUCT SELECTOR

Part Number	Voltage	Sensitivity	Type	Package
Z0607	600V	5mA	Standard	TO-92

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

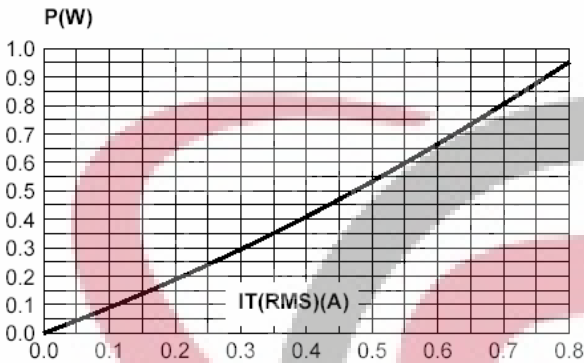


Fig. 2: RMS on-state current versus ambient temperature (full cycle).

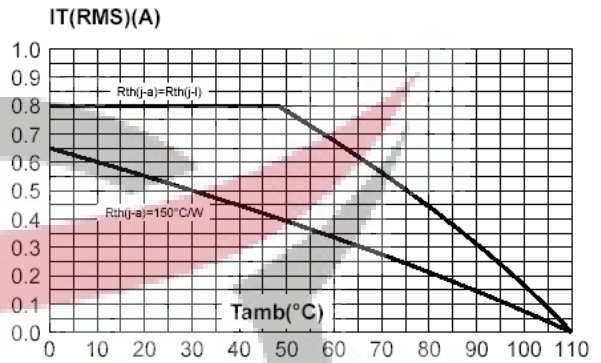


Fig. 3: Relative variation of thermal impedance junction to ambient versus pulse duration.

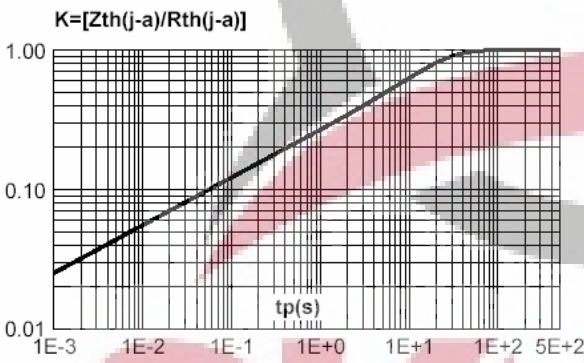


Fig. 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

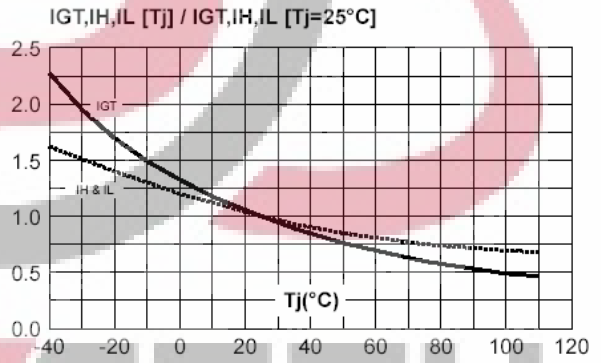


Fig. 5: Surge peak on-state current versus number of cycles.

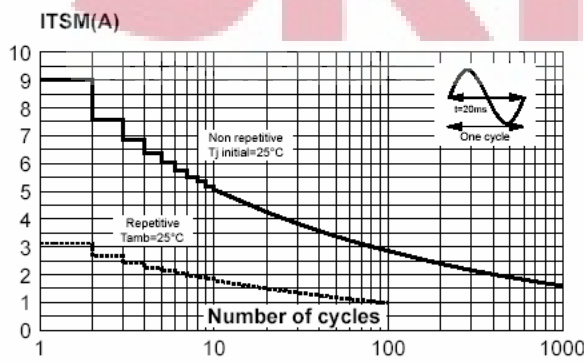


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I²t.

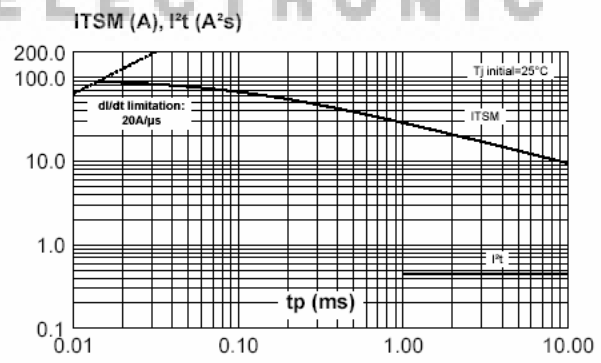


Fig. 7: On-state characteristics (maximum values).

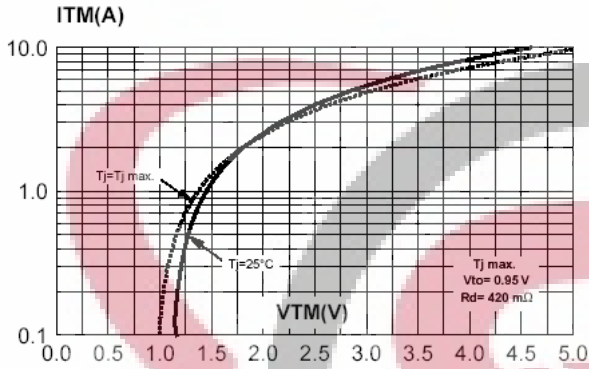


Fig. 8: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values).

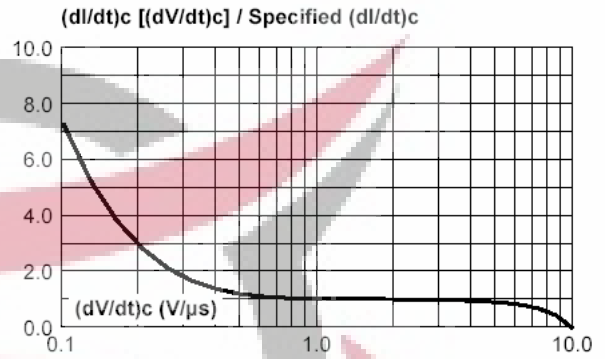


Fig. 9: Relative variation of critical rate of decrease of main current versus junction temperature.

